

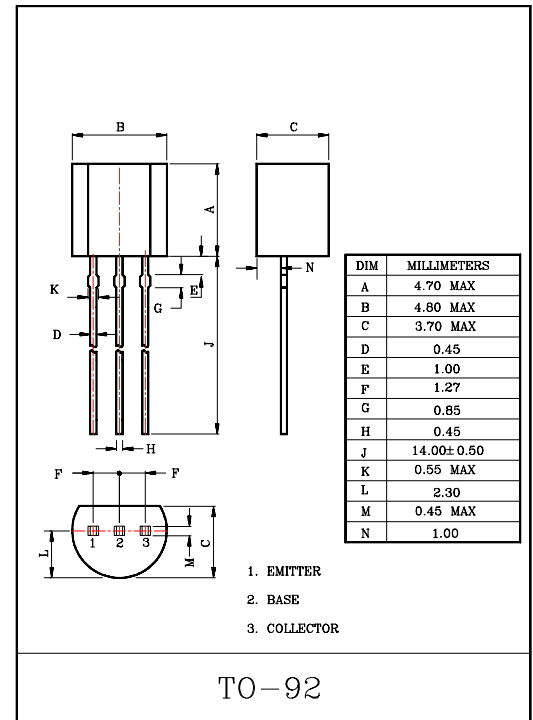
GENERAL PURPOSE APPLICATION.
HIGH VOLTAGE APPLICATION.

FEATURES

- High Collector Breakdwon Voltage
: $V_{CBO}=180V$, $V_{CEO}=160V$
- Low Leakage Current.
: $I_{CBO}=50nA(Max.)$ $V_{CB}=120V$
- Low Saturation Voltage
: $V_{CE(sat)}=0.2V(Max.)$ $I_C=50mA$, $I_B=5mA$
- Low Noise : $NF=8dB$ (Max.)

MAXIMUM RATINGS ($T_a=25^{\circ}C$)

CHARACTERISTIC	SYMBOL	RATING	UNIT
Collector-Base Voltage	V_{CBO}	180	V
Collector-Emitter Voltage	V_{CEO}	160	V
Emitter-Base Voltage	V_{EBO}	6	V
Collector Current	I_C	600	mA
Base Current	I_B	100	mA
Collector Power Dissipation	P_C	625	mW
Junction Temperature	T_j	150	$^{\circ}C$
Storage Temperature Range	T_{stg}	$-55 \sim 150$	$^{\circ}C$



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ELECTRICAL CHARACTERISTICS (Ta=25℃)

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Collector Cut-off Current	I_{CBO}	$V_{CB}=120V, I_E=0$	–	–	50	nA
		$V_{CB}=120V, I_E=0, T_a=100℃$	–	–	50	μA
Emitter Cut-off Current	I_{EBO}	$V_{EB}=4V, I_C=0$	–	–	50	nA
Collector-Base Breakdown Voltage	$V_{(BR)CBO}$	$I_C=0.1mA, I_E=0$	180	–	–	V
Collector-Emitter Breakdown Voltage *	$V_{(BR)CEO}$	$I_C=1mA, I_B=0$	160	–	–	V
Emitter-Base Breakdown Voltage	$V_{(BR)EBO}$	$I_E=10\mu A, I_C=0$	6	–	–	V
DC Current Gain *	$h_{FE}(1)$	$V_{CE}=5V, I_C=1mA$	80	–	–	
	$h_{FE}(2)$	$V_{CE}=5V, I_C=10mA$	80	–	250	
	$h_{FE}(3)$	$V_{CE}=5V, I_C=50mA$	30	–	–	
Collector-Emitter Saturation Voltage *	$V_{CE(sat)1}$	$I_C=10mA, I_B=1mA$	–	–	0.15	V
	$V_{CE(sat)2}$	$I_C=50mA, I_B=5mA$	–	–	0.2	
Base-Emitter Saturation Voltage *	$V_{BE(sat)1}$	$I_C=10mA, I_B=1mA$	–	–	1.0	V
	$V_{BE(sat)2}$	$I_C=50mA, I_B=5mA$	–	–	1.0	
Transition Frequency	f_T	$V_{CE}=10V, I_C=10mA, f=100MHz$	100	–	300	MHz
Collector Output Capacitance	C_{ob}	$V_{CB}=10V, I_E=0, f=1MHz$	–	–	6	pF
Input Capacitance	C_{ib}	$V_{BE}=0.5V, I_C=0, f=1MHz$	–	–	20	pF
Small-Signal Current Gain	h_{fe}	$V_{CE}=10V, I_C=1mA, f=1kHz$	50	–	200	
Noise Figure	NF	$V_{CE}=5V, I_C=250\mu A$ $R_g=1k\Omega, f=10Hz \sim 15.7kHz$	–	–	8	dB

*Pulse Test : Pulse Width $\leq 300\mu S$, Duty Cycle $\leq 2\%$